# **General Purpose Transistor**

# **NPN Silicon**

• Moisture Sensitivity Level: 1

• ESD Rating: Human Body Model: >4000 V

Machine Model: >400 V

• This is a Pb-Free Device

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	65	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current – Continuous	Ic	100	mAdc

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C	P <sub>D</sub>	265	mW
Derate above 25°C		2.1	mW/°C
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C	P <sub>D</sub>	640	mW
Derate above 25°C		5.1	mW/°C
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ heta JA}$	195	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

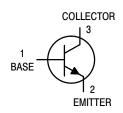
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



# ON Semiconductor®

http://onsemi.com



#### MARKING DIAGRAM



SOT-723 CASE 631AA STYLE 1



1B = Specific Device Code M = Date Code

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>		
BC846BM3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•		•	•	•
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA)	V <sub>(BR)CEO</sub>	65	_	_	V
Collector – Emitter Breakdown Voltage ( $I_C = 10 \mu A, V_{EB} = 0$ )	V <sub>(BR)</sub> CES	80	-	-	٧
Collector – Base Breakdown Voltage ( $I_C = 10 \mu A$ )	V <sub>(BR)CBO</sub>	80	-	-	٧
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 1.0 μA)	V <sub>(BR)EBO</sub>	6.0	-	-	٧
Collector Cutoff Current $(V_{CB} = 30 \text{ V})$ $(V_{CB} = 30 \text{ V}, T_A = 150^{\circ}\text{C})$	I <sub>CBO</sub>	-	- -	15 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ (I_C = 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ \text{V}) $ $ (I_C = 2.0 \ \text{mA}, \ V_{CE} = 5.0 \ \text{V}) $	h <sub>FE</sub>	_ 200	150 290	_ 450	_
Collector – Emitter Saturation Voltage ( $I_C$ = 10 mA, $I_B$ = 0.5 mA) ( $I_C$ = 100 mA, $I_B$ = 5.0 mA)	V <sub>CE(sat)</sub>	-	- -	0.25 0.6	٧
Base – Emitter Saturation Voltage ( $I_C$ = 10 mA, $I_B$ = 0.5 mA) ( $I_C$ = 100 mA, $I_B$ = 5.0 mA)	V <sub>BE(sat)</sub>	-	0.7 0.9	_ _	٧
Base – Emitter Voltage ( $I_C$ = 1.0 mA, $V_{CE}$ = 5.0 V) ( $I_C$ = 2.0 mA, $V_{CE}$ = 5.0 V) ( $I_C$ = 10 mA, $V_{CE}$ = 5.0 V)	V <sub>BE(on)</sub>	550 580 -	645 660 –	700 700 770	mV
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	100	-	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 V, f = 1.0 MHz)	C <sub>obo</sub>	-	-	4.5	pF
Noise Figure (I <sub>C</sub> = 0.2 mA, $V_{CE}$ = 5.0 Vdc, $R_S$ = 2.0 k $\Omega$ , f = 1.0 kHz, BW = 200 Hz)	NF	_	-	10	dB

#### **TYPICAL CHARACTERISTICS**

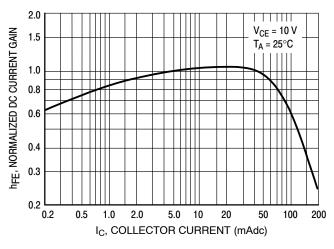


Figure 1. Normalized DC Current Gain

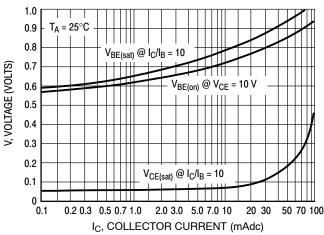


Figure 2. "Saturation" and "On" Voltages

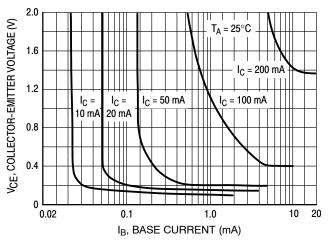


Figure 3. Collector Saturation Region

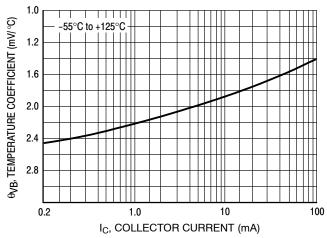


Figure 4. Base-Emitter Temperature Coefficient

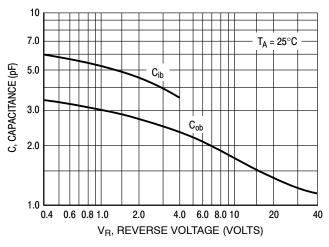


Figure 5. Capacitances

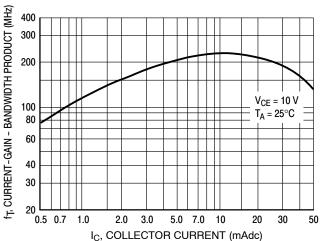


Figure 6. Current-Gain - Bandwidth Product

## **TYPICAL CHARACTERISTICS**

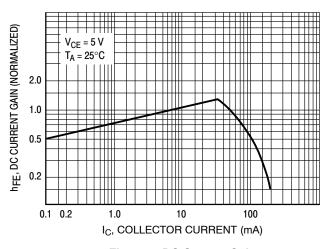


Figure 7. DC Current Gain

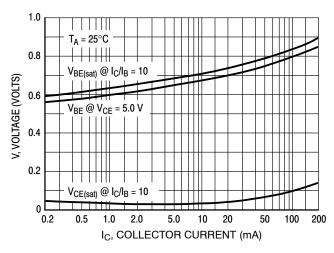


Figure 8. "On" Voltage

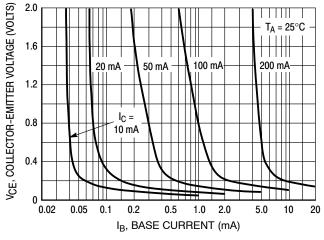


Figure 9. Collector Saturation Region

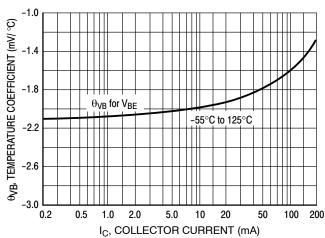


Figure 10. Base-Emitter Temperature Coefficient

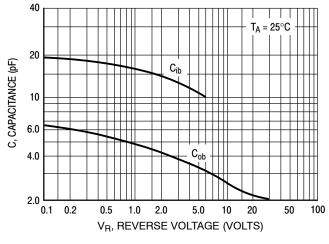


Figure 11. Capacitance

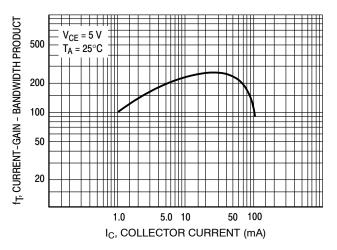
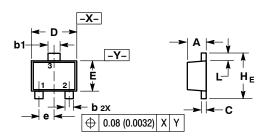


Figure 12. Current-Gain - Bandwidth Product

#### PACKAGE DIMENSIONS

SOT-723 CASE 631AA-01 ISSUE C



STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

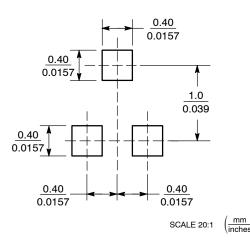
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- THICKNESS OF BASE MATERIAL.

  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

		MILLIMETERS			INCHES		
L	DIM	MIN	NOM	MAX	MIN	NOM	MAX
	Α	0.45	0.50	0.55	0.018	0.020	0.022
	q	0.15	0.21	0.27	0.0059	0.0083	0.0106
	b1	0.25	0.31	0.37	0.010	0.012	0.015
	С	0.07	0.12	0.17	0.0028	0.0047	0.0067
	D	1.15	1.20	1.25	0.045	0.047	0.049
	Е	0.75	0.80	0.85	0.03	0.032	0.034
Г	ø	0.40 BSC			C	.016 BS	С
	HΕ	1.15	1.20	1.25	0.045	0.047	0.049
Γ	٦	0.15	0.20	0.25	0.0059	0.0079	0.0098

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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